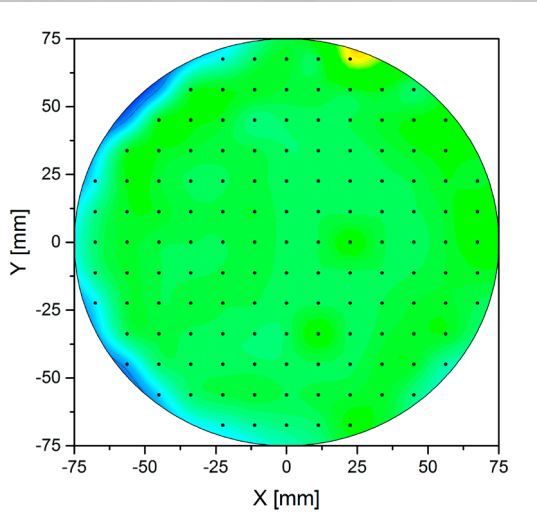


The best of both worlds
Single Wafer Control



Excellent wafer uniformities



Leading nitrogen doping uniformity
on 150 mm 4H-SiC
Sigma/mean = 2 % at 1E16 cm-3 (5 mm EE)

AIXTRON
Global Presence



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DEPOSITON SYSTEMS FOR COMPOUND SEMICONDUCTORS
AIX G5 WW C Planetary Reactor®
for 150 mm SiC

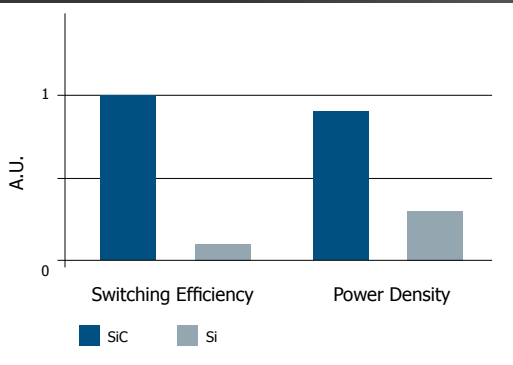
AIXTRON
Our technology. Your future.

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Our technology. Your future.

Best Performance for Next Generation SiC Power Electronics to address Global Mega Trends

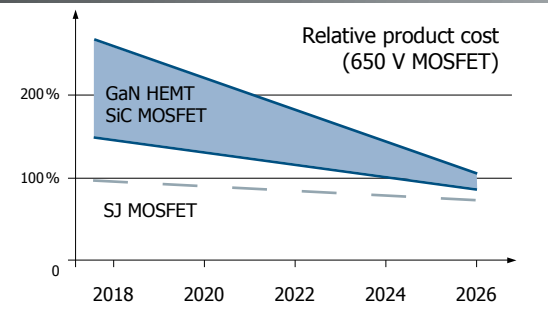
OPPORTUNITY

- ▶ 5 - 10 % higher efficiency compared to Si IGBT devices
- ▶ Superior switching & power density



CHALLENGE

- ▶ 2-3 x higher cost than Si
- ▶ 1-2 bn SiC power device market by 2023 in a larger 10+ bn total power market



AIX G5 WW C

The best of both worlds



The best of both worlds
Batch Productivity



AIX G5 WW C

- ▶ High throughput batch epitaxy with single wafer control
- ▶ Excelling in epitaxial layer performance
- ▶ Supporting the SiC power market ramp-up



YOUR BENEFITS

- ▶ Best in class throughput and epitaxial cost per wafer
- ▶ Single Wafer performance in batch configuration
- ▶ Si fab compatible automation

OUR SOLUTION

- ▶ Fast epitaxial processing
- ▶ Planetary Reactor® with hot wafer transfer
- ▶ Efficient gas utilization in growth chamber
- ▶ 8x150 mm wafer configuration with single wafer rotation
- ▶ Wafer level temperature control
- ▶ AutoSat feature for within batch uniformity
- ▶ Cassette-to-cassette wafer handling
- ▶ Susceptor component buffer station
- ▶ SECS-GEM factory interface

High capacity 8 x 150 mm

